



INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
ITO.0046US (P16201)

SERIAL NO.
10/633,872

APPLICANT(S):
Tyler A. Lowrey et al.

FILING DATE:
August 4, 2003

GROUP ART UNIT:
2827

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TL	A.	4,199,692	04/22/1980	Neale	—	—	—
TL	B.	5,536,947	07/16/1996	Klersy et al.	—	—	—
	C.						
	D.						

U.S. PATENT APPLICATION PUBLICATIONS

	E.	US 2004/0228159	11/18/2004	Kostylev et al.			
	F.						
	G.						
	H.						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
TL	I.	EP 1 489 623	12/22/2004	Europe				
TL	J.	WO 00/57498	09/28/2000	PCT				
TL	K.	WO 2004/055828	07/01/2004	PCT				
TL	L.	WO 2004/055899	07/01/2004	PCT				
TL	M.	WO 2005/017904	02/24/2005	PCT				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TL	N.	Yi-Chou Chen et al., <i>An Access-Transistor-Free (0T/1R) Non-Volatile Resistance Random Access Memory (RRAM) Using A Novel Threshold Switching, Self-Rectifying Chalcogenide Device</i> , Intl. Electron Devices Mtg. 2003, IEDM, Technical Digest, Washington, DC Dec. 8-10, 2003, New York, NY: IEEE, pgs. 905-908.					
TL	O.	Agostino Pirovano et al., <i>Low-Field Amorphous State Resistance And Threshold Voltage Drift In Chalcogenide Materials</i> , IEEE Transactions On Electron Devices, IEEE Inc., New York, NY, Vol. 51, No. 5, May 2004, pgs. 714-719.					
TL	P.	F. Pellizzer et al., <i>Novel μTrench Phase-Change Memory Cell For Embedded And Stand-Alone Non-Volatile Memory Applications</i> , VLSI Technology, 2004, Digest of Technical Papers 2004 Symposium, Honolulu, HI, June 15-17, 2004, Piscataway, NJ, IEEE, June 15, 2004, pgs. 18-19.					
	Q.						
	R.						

EXAMINER

Lowrey

DATE CONSIDERED

9/21/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.